

LL053BT1210

List

List.....	1
Package outline.....	2
Features.....	2
Applications.....	2
Mechanical data.....	2
Maximum ratings	2
Electrical characteristics.....	2
Rating and characteristic curves.....	3
Pinning information.....	4
Marking.....	4
Suggested solder pad layout.....	4
Suggested thermal profiles for soldering processes.....	5

LL053BT1210

2-Channel Ultra Low Capacitance ESD Protection Diodes Array 5.0V

Features

- Ultra-small package (1.2mm x 1.0mm x 0.50mm).
- Protects two data lines.
- Low capacitance : 0.2pF Typical (I/O to GND)
- IEC61000-4-2 (ESD) $\pm 25\text{KV}$ (Air), $\pm 17\text{KV}$ (Contact)
- IEC61000-4-2 (EFT) 40A (5/50ns)
- Cable discharge event (CDE).
- Low leakage current : $0.1\mu\text{A}$ @ V_{RWM} (Typical)
- Each I/O pin can withstand over 1000 ESD strikes for $\pm 8\text{KV}$ contact discharge.
- RoHS compliant.
- Suffix "-H" indicates Halogen-free parts, ex. LL053BT1210-H.

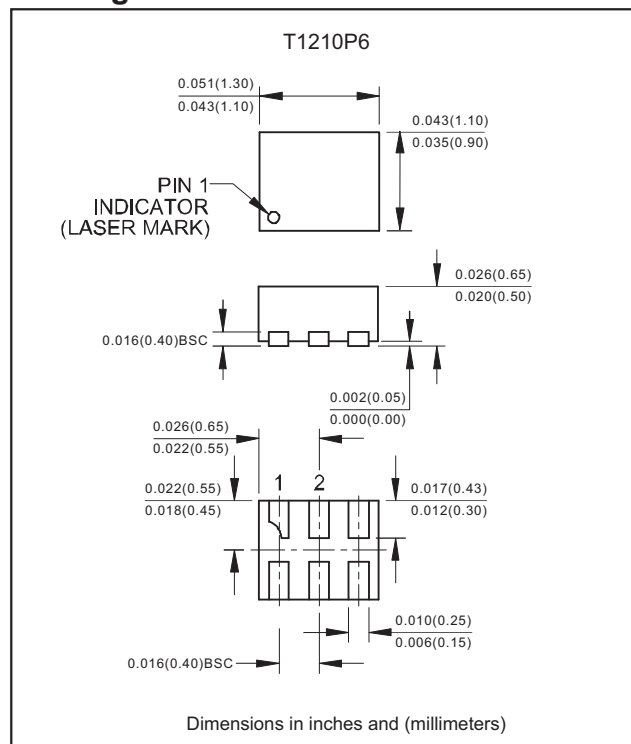
Applications

- Serial ATA.
- PCI Express.
- USB2.0 and data line protection.
- High definition multi-media interface (HDMI).

Mechanical data

- Flammability Rating: UL 94V-0.
- Terminal: Matte tin plated.
- Case : Molded plastic, T1210P6.
- Mounting Position : Any.

Package outline



Maximum ratings (at $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Peak pulse power ($t_p=8/20\mu\text{s}$)	P_{PP}	60	W
Peak pulse current ($t_p=8/20\mu\text{s}$)	I_{PP}	5	A
ESD per IEC 61000-4-2 (Contact)	V_{ESD}	± 17	KV
ESD per IEC 61000-4-2 (Air)		± 25	
Operating temperature	T_{OPT}	+125	$^\circ\text{C}$
Storage temperature	T_{STG}	-55 to +150	$^\circ\text{C}$

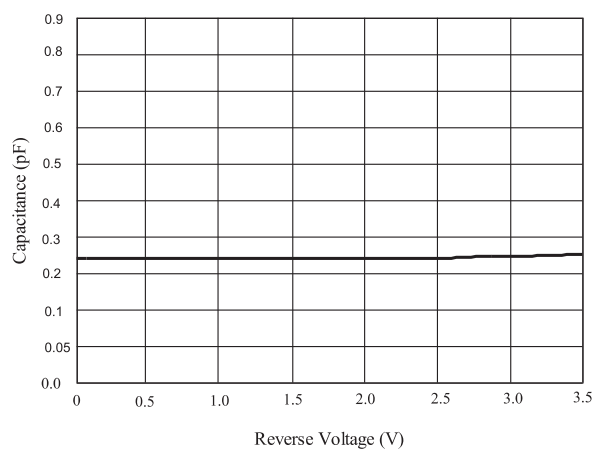
Electrical characteristics (at $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Conditions	Symbol	Min.	Typ.	Max.	Unit
Reverse stand-off voltage		V_{RWM}			5.0	V
Reverse leakage current	$V_{\text{RWM}}=5.0\text{V}$	I_{R}		0.1	1.0	μA
Reverse Breakdown voltage	$I_{\text{r}}=1\text{mA}$	V_{BR}	6.0		9.0	V
Clamping voltage	$I_{\text{PP}}=5\text{A}$, $t_p=8/20\mu\text{s}$ (I/O and GND)	V_{C}			12	V
Junction capacitance	$V_{\text{R}}=0\text{V}$, $f=1\text{MHz}$, (I/O and GND)	C_{ESD}		0.2	0.5	pF

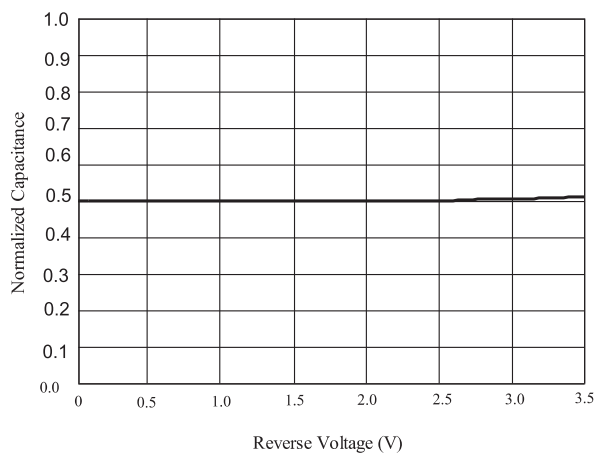
Note : 1. Measurements performed using a 100ns transmission line pulse (TLP) system.

Rating and characteristic curves(LL053BT1210)

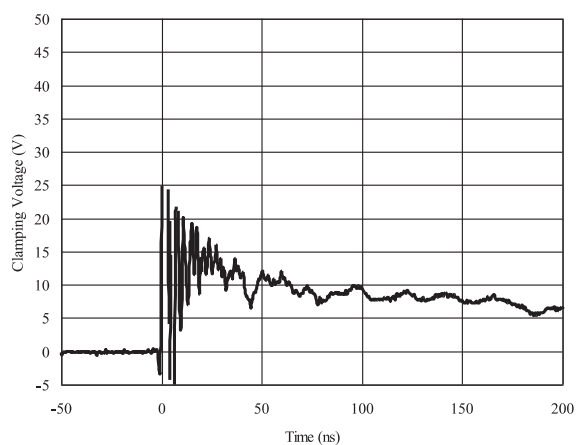
Capacitance vs. Reverse Voltage



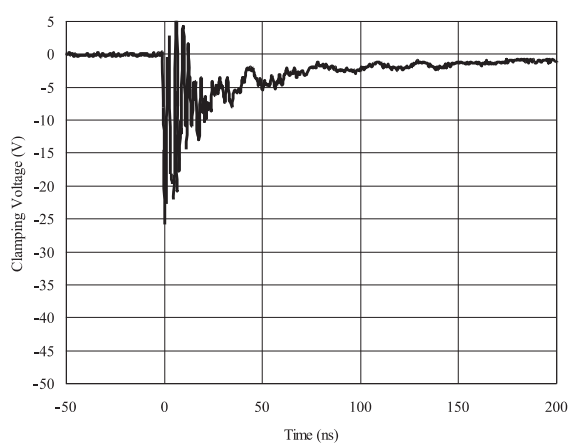
Normalized Capacitance vs. Reverse Voltage



**ESD Clamping of I/O to GND
(+8kV Contact per IEC 61000-4-2)**



**ESD Clamping of I/O to GND
(-8kV Contact per IEC 61000-4-2)**

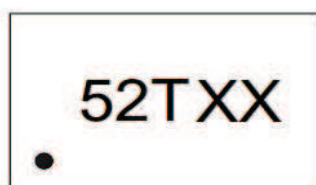


LL053BT1210

Pinning information

Pin Configuration	Simplified outline	Circuit Diagram
1 GND 2, 3, NC 4, 5 I/O Line 6 VCC		

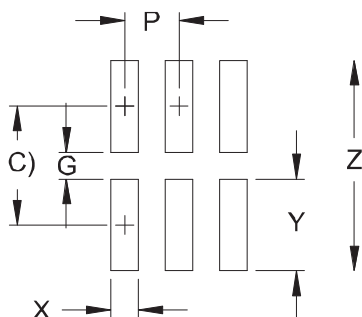
Marking



Note:

- (1) " 52T " is part number, fixed.
- (2) "XX" is the internal code.

Suggested solder pad layout

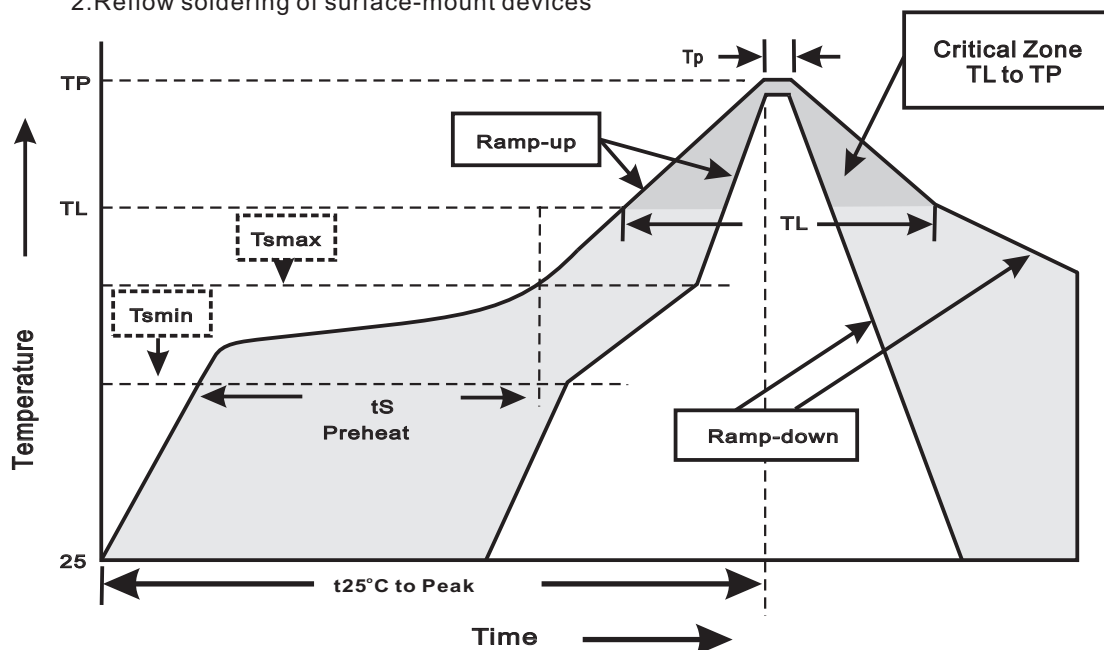


DIM	DIMENSIONS	
	INCHES	MILLIMETERS
C	(.034)	(0.875)
G	.008	0.20
P	.016	0.40
X	.008	0.20
Y	.027	0.675
Z	.061	1.55

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Suggested thermal profiles for soldering processes

- 1.Storage environment: Temperature=5°C~40°C Humidity=55%±25%
- 2.Reflow soldering of surface-mount devices



3.Reflow soldering

Profile Feature	Soldering Condition
Average ramp-up rate(T_L to T_P)	$<3^{\circ}\text{C}/\text{sec}$
Preheat -Temperature Min(T_{smin}) -Temperature Max(T_{smax}) -Time(min to max)(t_s)	150°C 200°C 60~120sec
T_{smax} to T_L -Ramp-upRate	$<3^{\circ}\text{C}/\text{sec}$
Time maintained above: -Temperature(T_L) -Time(t_L)	217°C 60~260sec
Peak Temperature(T_P)	255°C-0/+5°C
Time within 5°C of actual Peak Temperature(t_P)	10~30sec
Ramp-down Rate	$<6^{\circ}\text{C}/\text{sec}$
Time 25°C to Peak Temperature	$<6\text{minutes}$